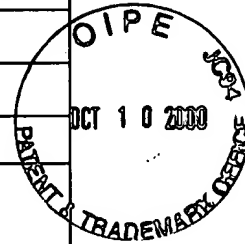


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INFORMATION
DISCLOSURE
STATEMENT

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Applicant(s): Whonchee Lee et al.

Filing Date: April 26, 2000

Group: 1746

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	SubClass	Filing Date If Appropriate
sl	4,528,066	07/09/85	Merkling et al.	438	696	
sl	5,010,032	04/23/91	Tang et al.	438	228	
sl	5,047,367	09/10/91	Wei et al.	438	607	
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FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	SubClass	Translation	
						Yes	No
	NONE						

OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

sl	Goto et al., "Optimization of Salicide Processes for sub 0.1-μm CMOS Devices", 1994 Symposium on VLSI Technology Digest of Technical Papers, pgs. 119-120 (1994).
sl	Ohguro et al., "Nitrogen-doped nickel monosilicide technique for deep submicron CMOS salicide", International Electron Devices Meeting, Washington, D.C., December 10-13, 1995, pgs. 10.3.1-10.3.4.

EXAMINER

sl

Date Considered

12/26/00

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.